CLAIMS

1. An Al wiring material containing at least Sc, ~~and~~ Zr and Ni so as to satisfy

$0.01 \leq x1 \leq 0.5$, ~~and~~

$0.01 \leq x2 \leq 0.3$, and

$10 \leq x3 < 200$

where x1 is a content of Sc [% by weight], ~~and~~ x2 is a content of Zr [% by weight] and x3 is a content of Ni [ppm by weight],

with the balance comprising Al,

wherein,

a wire diameter is equal to or larger than 50 μm and equal to or smaller than 600 μm.

2. The Al wiring material according to claim 1, further ~~containing Ni so as to satisfy $10 \leq x3 \leq 500$ where x3 is a content of Ni [ppm by weight]~~ wherein an average crystal grain diameter at a cross section (C cross section) perpendicular to a wire longitudinal direction is equal to or larger than 1 μm and equal to or smaller than 50 μm.

3. The Al wiring material according to claim 1 or 2, wherein x1 and x2 satisfy a relation of $x2/x1 > 0.5$.

4. The Al wiring material according to any one of claims 1 to 3, wherein Vickers hardness of a longitudinal axis part of the Al wiring material is 40 Hv or less.

5. The Al wiring material according to any one of claims 1 to 4, wherein the Al wiring material has been subjected to a thermal refining heat treatment at 580 to 640°C for 30 seconds or less.

6. The Al wiring material according to any one of claims 1 to 5, wherein the Al wiring material does not have a coating that contains a metal other than Al as a main component.

7. The Al wiring material according to any one of claims 1 to 6, wherein the Al wiring material is a bonding wire.

8. The Al wiring material according to any one of claims 1 to 7, wherein the Al wiring material is subjected to aging heat treatment at 250 to 400°C for 30 to 60 minutes after being connected to a member to be connected.

9. A semiconductor device comprising the Al wiring material according to any one of claims 1 to 8.